

DESCRIPTION

The MXND805 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It can be used in a wide variety of applications.

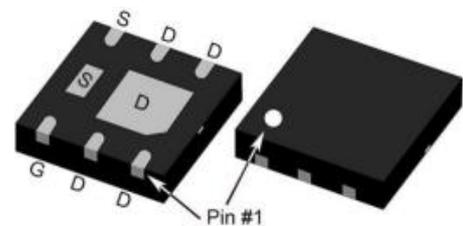
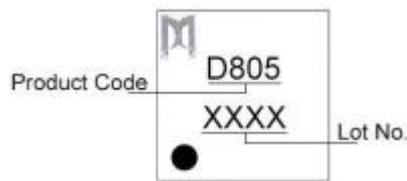
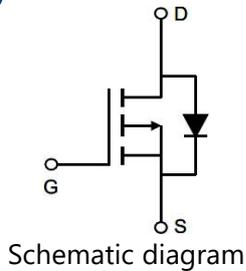
GENERAL FEATURES

- $V_{DS}=-12V$, $I_D=-8.5A$
 $R_{DS(ON)}(Typ.)=19m\Omega$ @ $V_{GS}=-2.5V$
 $R_{DS(ON)}(Typ.)=14m\Omega$ @ $V_{GS}=-4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

APPLICATION

- PWM applications
- Load switch
- Power management
- Battery Protection

PINOUT



ORDERING INFORMATION

| Part Number | Marking | Storage Temperature | Package | Devices Per Reel |
|-------------|---------|---------------------|------------|------------------|
| MXND805 | D805 | -55°C to 150°C | UDFN2X2-6L | - |

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|----------------|------------|------|
| Drain-Source Voltage | V_{DS} | -12 | V |
| Gate-Source Voltage | V_{GS} | ± 12 | V |
| Drain Current-Continuous | I_D | -8.5 | A |
| Pulsed Drain Current ^(Note1) | I_{DM} | -32 | A |
| Maximum Power Dissipation | P_D | 2.8 | W |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 150 | °C |

THERMAL RESISTANCE

| | | | |
|--|-----------------|----|------|
| Thermal Resistance, Junction-to-Ambient ^(Note2) | $R_{\theta JA}$ | 45 | °C/W |
|--|-----------------|----|------|

Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.



ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|-----------|--------|------------|-----|-----|-----|------|
|-----------|--------|------------|-----|-----|-----|------|

Off Characteristics

| | | | | | | |
|---------------------------------|------------|-----------------------------|---|-----|-----------|---------|
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=-250\mu A$ | - | -12 | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=-12V, V_{GS}=0V$ | - | - | -1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 12V, V_{DS}=0V$ | - | - | ± 100 | nA |

On Characteristics (Note3)

| | | | | | | |
|----------------------------------|--------------|--------------------------------|------|------|------|-----------|
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=-250\mu A$ | -0.4 | -0.7 | -1.2 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}=-2.5V, I_D=-5A$ | - | 19 | 25 | $m\Omega$ |
| | | $V_{GS}=-4.5V, I_D=-6A$ | - | 14 | 18 | $m\Omega$ |
| Forward Transconductance | g_{FS} | $V_{DS}=-5V, I_D=-6A$ | - | 33 | - | S |

Dynamic Characteristics (Note4)

| | | | | | | |
|------------------------------|-----------|-----------------------------------|---|------|---|------|
| Input Capacitance | C_{iss} | $V_{DS}=-10V, V_{GS}=0V, F=10KHz$ | - | 1770 | - | pF |
| Output Capacitance | C_{oss} | | - | 410 | - | pF |
| Reverse Transfer Capacitance | C_{rss} | | - | 390 | - | pF |

Switching Characteristics (Note4)

| | | | | | | |
|---------------------|--------------|---|--------------------------------------|----|----|----|
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=-10V, R_L=1\Omega, V_{GS}=-4.5V, R_G=3\Omega$ | - | 11 | - | nS |
| Turn-on Rise Time | t_r | | - | 25 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 70 | - | nS |
| Turn-Off Fall Time | t_f | | - | 42 | - | nS |
| Total Gate Charge | Q_g | | $V_{DS}=-10V, I_D=-6A, V_{GS}=-4.5V$ | - | 15 | - |
| Gate-Source Charge | Q_{gs} | - | | 4 | - | nC |
| Gate-Drain Charge | Q_{gd} | - | | 7 | - | nC |

Drain-Source Diode Characteristics

| | | | | | | |
|-------------------------------|----------|----------------------|---|---|------|---|
| Diode Forward Voltage (Note3) | V_{SD} | $V_{GS}=0V, I_S=-2A$ | - | - | -1.2 | V |
| Diode Forward Current (Note2) | I_S | | - | - | -3.5 | A |

Note 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

Note 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

Note 4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 1. Switching Test Circuit

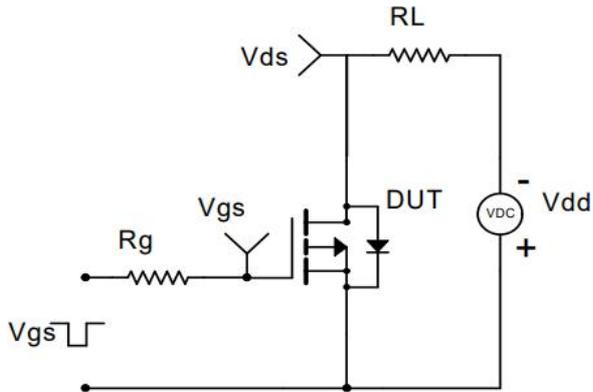


Figure 2. Switching Waveform

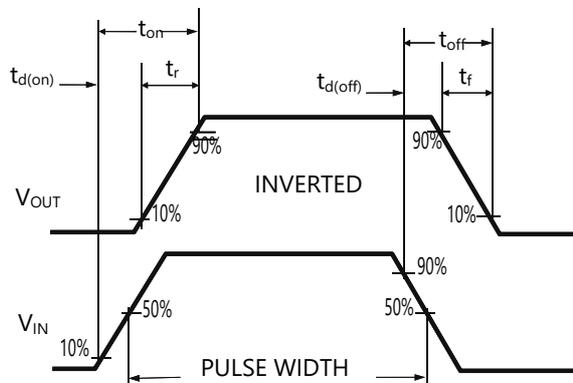


Figure 3. Power De-rating

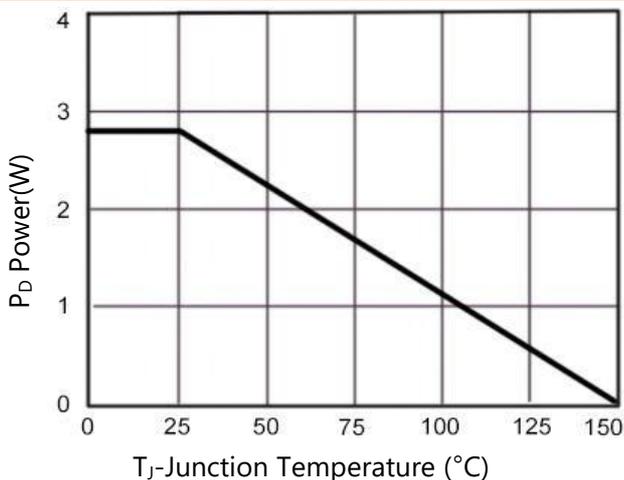


Figure 4. Drain Current

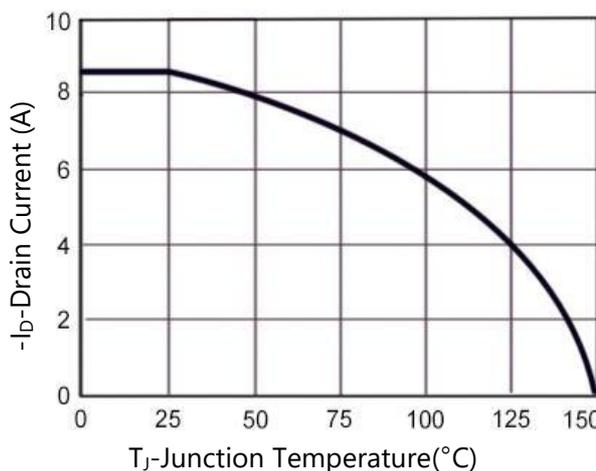


Figure 5. Output Characteristics

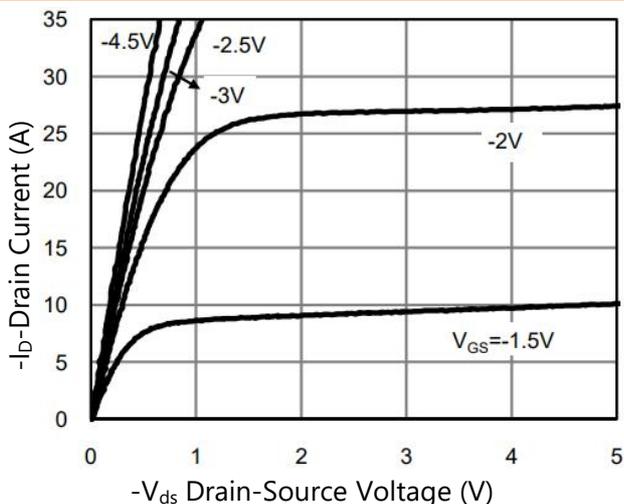
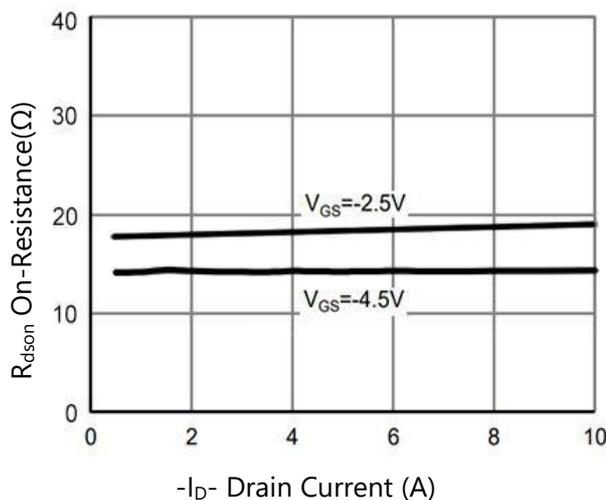


Figure 6. Rds(on) vs Drain Current



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 7. Transfer Characteristics

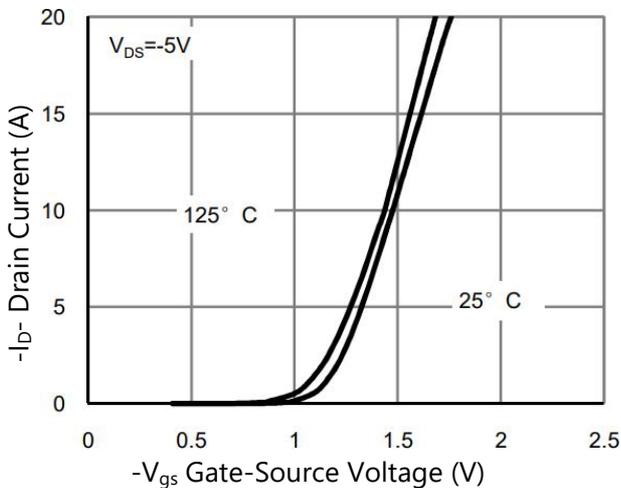


Figure 8. R_{dson} vs Junction Temperature

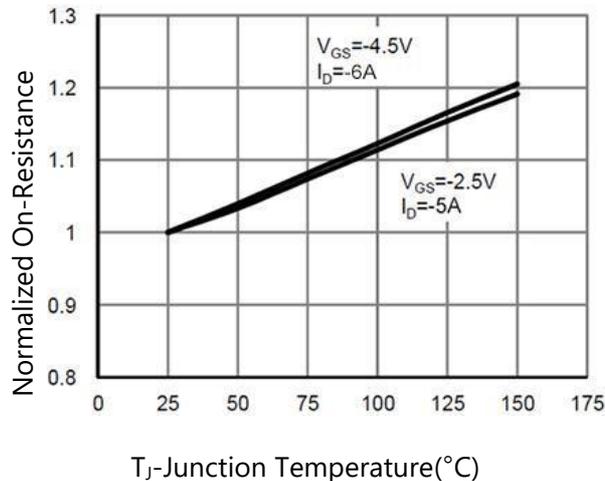


Figure 9. R_{dson} vs V_{gs}

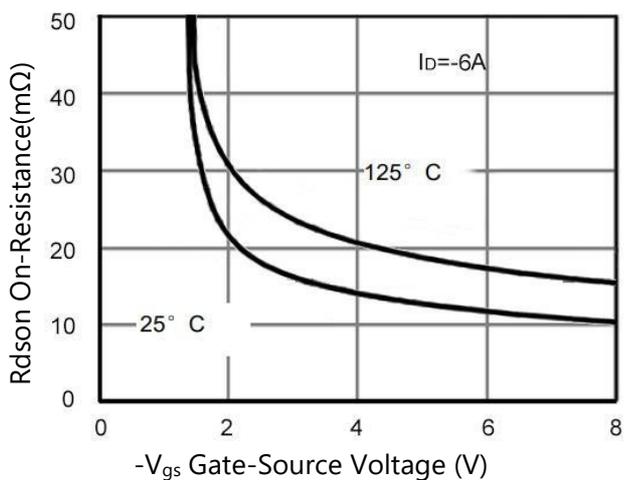


Figure 10. Capacitance vs V_{ds}

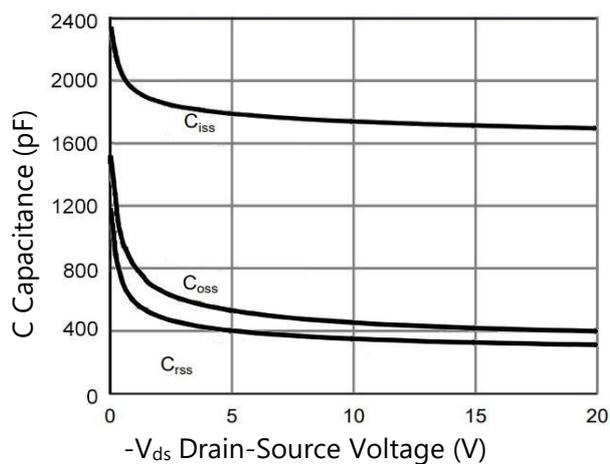


Figure 11. Gate Charge

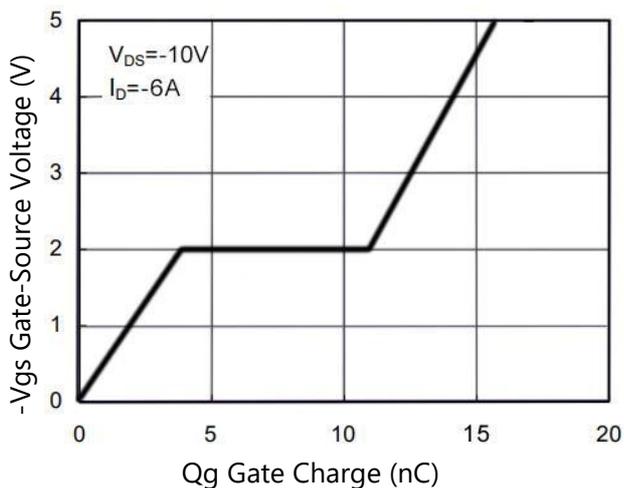
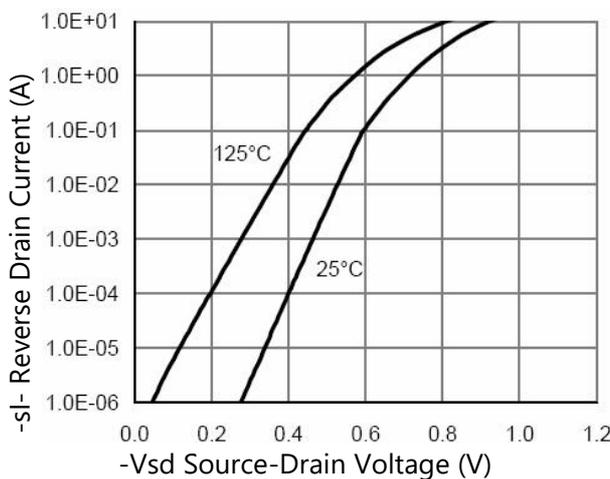


Figure 12. Source- Drain Diode Forward





TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 13. Safe Operation Area

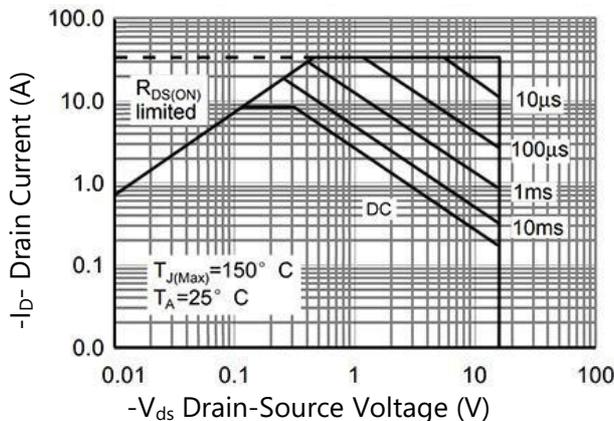
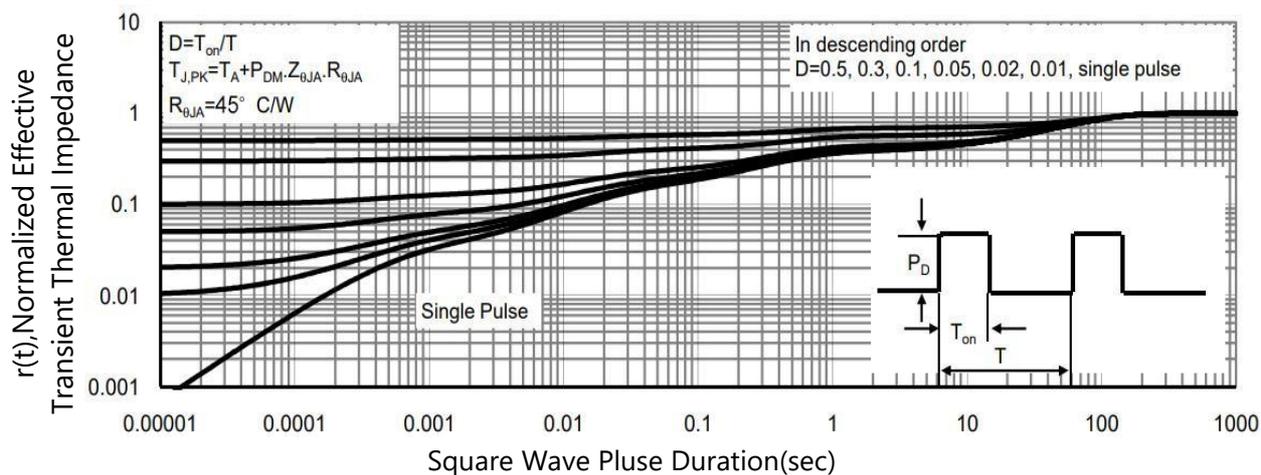
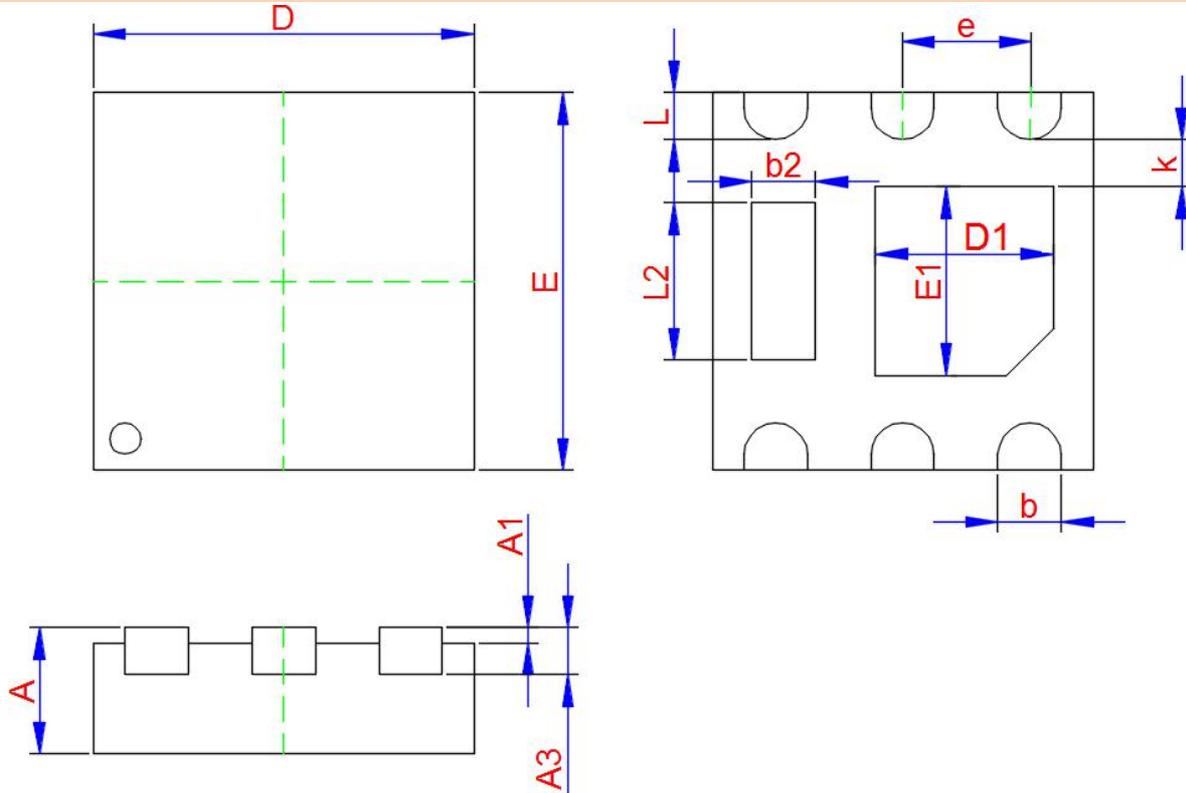


Figure 14. Normalized Maximum Transient Thermal Impedance



PACKAGE INFORMATION

UDFN2X2-6L



| Symbol | Dimensions In Millimeters | | |
|--------|---------------------------|-------|-------|
| | Min. | Typ. | Max. |
| A | 0.450 | 0.500 | 0.550 |
| A1 | 0.000 | - | 0.050 |
| A3 | 0.120 | 0.150 | 0.190 |
| D | 1.950 | 2.000 | 2.050 |
| E | 1.950 | 2.000 | 2.050 |
| D1 | 0.970 | 1.000 | 1.030 |
| E1 | 0.970 | 1.000 | 1.030 |
| b | 0.250 | 0.300 | 0.350 |
| L | 0.200 | 0.250 | 0.300 |
| b2 | 0.250 | 0.300 | 0.350 |
| L2 | 0.750 | 0.800 | 0.850 |
| k | 0.250MIN. | | |
| e | 0.650TYP. | | |